## **CLAIMS**

- An electroluminescent element comprising:
  - a pair of electrodes facing each other; and
- at least one phosphor layer formed between the pair of electrodes, wherein the phosphor layer includes a phosphor semiconductor with a wide band-gap.
- 2. The electroluminescent element according to claim 1, wherein the phosphor layer has a laminated structure of a phosphor layer and a semiconductor layer with wide band-gap.
- 3. The electroluminescent element according to claim 2, further comprising at least one transparent conductive layer interposed between the pair of electrodes.
- 4. The electroluminescent element according to claim 3, wherein the transparent conductive layer is a partially discontinuous layer.
- 5. The electroluminescent element according to any one of claims 2 to 4, wherein at least one of the phosphor layer and the semiconductor layer constituting the phosphor layer is a partially discontinuous layer.
- 6. The electroluminescent element according to claim 1, wherein the phosphor layer includes a phosphor particle in each of which at least a part of a surface thereof is covered with a semiconductor having a wide band-gap.

- 7. The electroluminescent element according to claim 1, wherein the phosphor layer includes a phosphor particle in each of which substantially all surface thereof is covered with a semiconductor having wide band-gap.
- 8. The electroluminescent element according to claim 1, wherein the phosphor layer is so configured that the phosphor particles, in each of which at least a part of a surface thereof is covered with a semiconductor having wide band-gap, are dispersed in a matrix material.
- 9. The electroluminescent element according to claim 1, wherein the phosphor layer is so configured that the phosphor particles, in each of which substantially all surface thereof is covered with a semiconductor having a wide band-gap, are dispersed within a matrix material.
- 10. The electroluminescent element according to claim 8 or 9, wherein the matrix material is a transparent conductor.
- 11. The electroluminescent element according to any one of claims 1 to 10, wherein the semiconductor constituting the phosphor layer has a band-gap causing to emit light of a shorter wavelength than blue light by applying an electric field.
- 12. The electroluminescent element according to any one of claims 1 to 10, wherein the semiconductor constituting the phosphor layer has a band-gap of

## 2.0eV or more.

- 13. The electroluminescent element according to any one of claims 1 to 10, wherein the semiconductor constituting the phosphor layer has a band-gap of 2.5eV or more.
- 14. The electroluminescent element according to any one of claims 11 to 13, wherein the semiconductor is so configured that a main component thereof is a 13<sup>th</sup>-15<sup>th</sup> group compound semiconductor, a mixed crystal thereof, or a mixture thereof in which a partial segregation is allowed.
- 15. The electroluminescent element according to any one of claims 11 to 13, wherein the semiconductor is so configured that a main component thereof is a 12<sup>th</sup>-16<sup>th</sup> group compound semiconductor, a mixed crystal thereof, or a mixture thereof in which a partial segregation is allowed.
- 16. The electroluminescent element according to any one of claims 11 to 13, wherein the semiconductor is so configured that a main component thereof is a 2<sup>nd</sup>-16<sup>th</sup> group compound semiconductor, a mixed crystal thereof, or a mixture thereof in which a partial segregation is allowed.
- 17. The electroluminescent element according to any one of claims 11 to 13, wherein the semiconductor is so configured that a main component thereof is a 12<sup>th</sup>-13<sup>th</sup>-16<sup>th</sup> group compound semiconductor, a mixed crystal thereof, or a mixture thereof in which a partial segregation is allowed.

- 18. The electroluminescent element according to any one of claims 11 to 13, wherein the semiconductor is so configured that a main component thereof is a 11<sup>th</sup>-13<sup>th</sup>-16<sup>th</sup> group compound semiconductor, a mixed crystal thereof, or a mixture thereof in which a partial segregation is allowed.
- 19. The electroluminescent element according to any one of claims 11 to 13, wherein the semiconductor is so configured that a 12<sup>th</sup>-14<sup>th</sup>-15<sup>th</sup> group compound semiconductor, a mixed crystal thereof, or a mixture thereof in which a partial segregation is allowed.
- 20. The electroluminescent element according to any one of claims 1 to 19, further comprising an electron transport layer between the phosphor layer and at least one of the electrodes.
- 21. The electroluminescent element according to any one of claims 1 to 20, wherein the pair of electrodes are positive electrode and negative electrode.
- 22. The electroluminescent element according to claim 21, wherein at least one semiconductor layer constituting the phosphor layer is located nearer the negative electrode side than the phosphor layer.
- 23. The electroluminescent element according to any one of claims 1 to 22, further comprising a thin film transistor connected with one of the pair of electrodes.

## 24. A display device comprising:

an electroluminescent array in which electroluminescent elements according to claim 23 are arranged in two dimensions;

a plurality of x electrodes, in parallel with each other, extending in a first direction in parallel with a face of the electroluminescent array; and

a plurality of y electrodes extending in parallel with a second direction, orthogonal to the first direction, in parallel with the face of the electroluminescent array, wherein the thin film transistor of the electroluminescent array is connected with the x electrode and the y electrode, respectively.